



<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT(S)</b> (Use as many sheets as necessary)	<b>Form 1449/PTO</b>		<b>COMPLETE IF KNOWN</b>	
	Application Number		10/533,822	
	Filing Date		August 31, 2005	
	First Named Inventor		Mino Green	
	Art Unit		2815	
	Examiner Name		Jami M. Valentine	
Sheet 1 of 3		Attorney Docket No.		KSTR 2 00004

### U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	Document No. Number-Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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### FOREIGN PATENT DOCUMENTS

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### OTHER -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	AC	Ohara et al, "A thin film silicon...", J. Power Sources 136 (2004), pp303-6	
	AD	J.P. Maranchi et al, Interfacial properties of the....", J. Electrochem. Soc. 153(6) A1246, 2006	
	AE	M. Green et al, "Structured Silicon Anodes for...", Electrochem and solid-state Letters 6, A75-79, 2003	
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	AG	Y. Liu et al. A novel method of fabricating porous silicon material: ultrasonically enhanced anodic electrochemical etching. Solid State Communications 127 (2003) 583-588	
	AH	W. Lang. Silicon Micromachining Technology. Materials Science and Engineering R17 (1996) 1-55	
	AI	T. Qiu et al, From Si nanotubes to nanowires: Synthesis, characterization, and self-assembly, Journal of Crystal Growth 277 (2005) 143-148	
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	AM	H.-C. Shin et al. Porous silicon negative electrodes for rechargeable lithium batteries, Journal of Power Sources 139 (2005) 314-320	
	AN	K. Tokoro, D. Uchikawa, M. Shikida, and K. Sato. Anisotropic Etching Properties of Silicon in KOH and TMAH Solutions. Proceedings of the 1998 International Symposium on Micromechatronics and Human Science, 1998. MHS '98. 25-28 Nov. 1998 pp. 65 - 70	

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	BC	S-H Kim, S-H Lee, H-T Lim, Y-K Kim, S-K Lee. (110) silicon etching for high aspect ratio comb structures 1997 6th International Conference on Emerging Technologies and Factory Automation Proceedings, 1997. ETFA '97., 9-12 Sept. 1997 pp.248-252			
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	BF	J. B. Chang et al, "Ultrafast growth of single-crystalline Si nanowires", Materials Letters 60 (2006) 2125-2128			
	BG	R. Wagner, W. Ellis. "Vapor-liquid solid mechanism of single crystal growth", Applied Physics Letters Vol4, No.5 March 1964, 89-90			
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	BM	H.F. Yan et al., "Growth of amorphous silicon...", Chemical Physics Letters 323 (2000) 224-228			

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	CC	Y.Y. Wong et al., "Controlled growth of silicon...", Science and Technology of Advanced Materials 6 (2005) 330-4			
	CD	Z.Y. Zhang et al. Catalytic growth of a-FeSi <sub>2</sub> and silicon nanowires. Journal of Crystal Growth 280 288 (2005) 286-291			
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	CJ				
	CK				
	CL				
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Examiner Signature	/Jami Valentine/	Date Considered	03/21/2008
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